

2-pack-integrated intelligent Power System

Power Section

SKiiP 1013GB172-2DL

Preliminary Data

Features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532

- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		1700		V
$V_{CC}^{1)}$	Operating DC link voltage	1200		V
V_{GES}		± 20		V
I_C	$T_s = 25 \text{ (70)}^\circ\text{C}$	1000 (750)		A
Inverse diode				
$I_F = -I_C$	$T_s = 25 \text{ (70)}^\circ\text{C}$	830 (630)		A
I_{FSM}	$T_j = 150^\circ\text{C}$, $t_p = 10 \text{ ms}$; sin	6900		A
I^2t (Diode)	Diode, $T_j = 150^\circ\text{C}$, 10 ms	238		kA ² s
T_j (T_{stg})		- 40 ... + 150 (125)		°C
V_{isol}	rms, AC, 1 min, main terminals to heat sink	4000		V
$I_{AC\text{-terminal}}$	per AC terminal, rms, $T_s = 70^\circ\text{C}$,	400		A
	$T_{\text{terminal}} \leq 115^\circ\text{C}$			

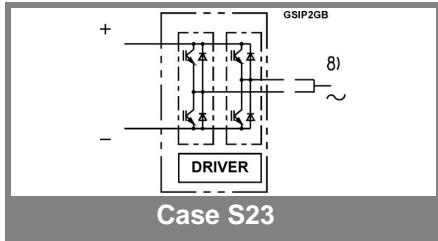
Characteristics		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
IGBT				
V_{CEsat}	$I_C = 600 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$; measured at terminal	1,9 (2,2)	2,4	V
V_{CEO}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	1 (0,9)	1,2 (1,1)	V
r_{CE}	$T_j = 25 \text{ (125)}^\circ\text{C}$; at terminal	1,5 (2,1)	1,9 (2,5)	mΩ
I_{CES}	$V_{GE} = 0 \text{ V}$, $V_{CE} = V_{CES}$, $T_j = 25 \text{ (125)}^\circ\text{C}$	2,4 (144)		mA
$E_{on} + E_{off}$	$I_C = 600 \text{ A}$, $V_{CC} = 900 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 1200 \text{ V}$	390		mJ
$R_{CC+EE'}$	terminal chip, $T_j = 25^\circ\text{C}$	0,25		mΩ
L_{CE}	top, bottom	6		nH
C_{CHC}	per phase, AC-side	3,4		nF
Inverse diode				
$V_F = V_{EC}$	$I_F = 600 \text{ A}$, $T_j = 25 \text{ (125)}^\circ\text{C}$ measured at terminal	2 (1,8)	2,15	V
V_{TO}	$T_j = 25 \text{ (125)}^\circ\text{C}$	1,1 (0,8)	1,2 (0,9)	V
r_T	$T_j = 25 \text{ (125)}^\circ\text{C}$	1,5 (1,7)	1,6 (1,8)	mΩ
E_{rr}	$I_C = 600 \text{ A}$, $V_{CC} = 900 \text{ V}$ $T_j = 125^\circ\text{C}$, $V_{CC} = 1200 \text{ V}$	72		mJ
		86		mJ

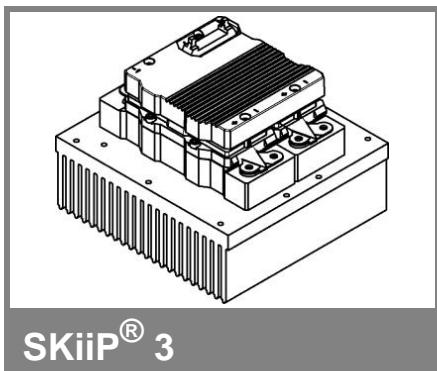
Mechanical data				
M_{dc}	DC terminals, SI Units	6	8	Nm
M_{ac}	AC terminals, SI Units	13	15	Nm
w	SKiiP® 3 System w/o heat sink		1,7	kg
w	heat sink		5,4	kg

Thermal characteristics (PX 16 heat sink with fan SKF 16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)

$R_{th(j-s)I}$	per IGBT	0,03	K/W
$R_{th(j-s)D}$	per diode	0,058	K/W
Z_{th}	R_i (mK/W) (max. values)	$\tau_{ai}(s)$	
	1 2 3 4	1 2 3 4	
$Z_{th(j-r)I}$	9,8 16,4 3,8 0	0,37 0,06 0,01 1	
$Z_{th(j-r)D}$	10 24 24 36	50 5 0,25 0,04	
$Z_{th(r-a)}$	4,3 20,3 7,1 2,3	160 53 9 0,4	

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2-pack-integrated intelligent Power System

**2-pack
integrated gate driver
SKiiP 1013GB172-2DL**

Preliminary Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protection against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute Maximum Ratings		$T_a = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified		
Symbol	Conditions	Values		Units
V_{S2}	unstabilized 24 V power supply	30		V
V_i	input signal voltage (high)	15 + 0,3		V
dv/dt	secondary to primary side	75		kV/ μ s
V_{isollo}	input / output (AC, rms,)	4000		V
V_{isolPD}	partial discharge extinction voltage, rms, Q_{PD} pC;	1500		V
V_{isol12}	output 1 / output 2 (AC, rms,)	1500		V
f_{sw}	switching frequency	14		kHz
f_{out}	output frequency for $I=I_C$; sin.	1		kHz
$T_{op} (T_{stg})$	operating / storage temperature	- 40 ... + 85		°C

Characteristics		$T_a = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
V_{S2}	supply voltage non stabilized	13	24	30
I_{S2}	$V_{S2} = 24 \text{ V}$	$320+23*f/\text{kHz}+0,00022*(I_{AC}/A)^2$		
V_{IT+}	input threshold voltage (High)	12,3		
V_{IT-}	input threshold voltage (Low)	4,6		V
R_{IN}	input resistance	10		
C_{IN}	input capacitance	1		
$t_{d(on)IO}$	input-output turn-on propagation time	1,3		
$t_{d(off)IO}$	input-output turn-off propagation time	1,3		
$t_{pERRRESET}$	error memory reset time	9		
t_{TD}	top / bottom switch interlock time	3,3		
$I_{analogOUT}$	max. 5mA; 8 V corresponds to 15 V supply voltage for external components	1000		
I_{s1out}	max. load current	50		
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10 \text{ V}$)	1250		
T_{tp}	over temperature protection	110		120
U_{DCTRIP}	U_{DC} -protection ($U_{analog OUT} = 9 \text{ V}$); (option for GB types)	not implemented		

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